

isc P-Channel MOSFET Transistor

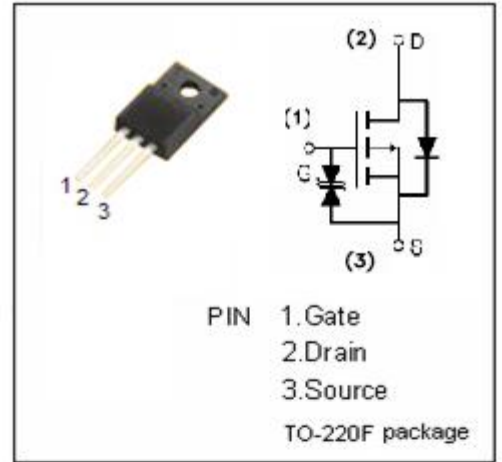
2SJ376

DESCRIPTION

- Low Drain-Source ON Resistance
- High Forward Transfer Admittance
- Low Leakage Current
- Enhancement-Mode

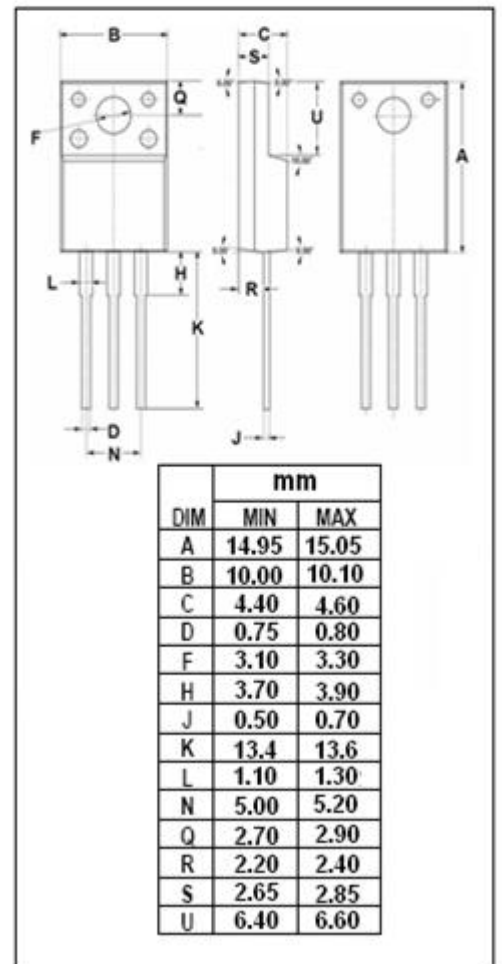
APPLICATIONS

- High speed switching application
- Switching regulator ,DC-DC converter and Motor drive application



ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	-60	V
V _{GS}	Gate-Source Voltage	±15	V
I _D	Drain Current-continuous@ TC=37°C	-30	A
P _{tot}	Total Dissipation@TC=25°C	50	W
T _j	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance,Junction to Case	3.1	°C/W
R _{th j-a}	Thermal Resistance,Junction to Ambient	75	°C/W

isc P-Channel Mosfet Transistor**2SJ376****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = -1mA	-60		V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D = -1mA	-1.0	-2.0	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} = -10V; I _D = -15A		0.045	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = -12V; V _{DS} = 0		-10	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -60V, V _{GS} = 0		-0.1	mA
V _{SD}	Diode Forward Voltage	I _F =-20A; V _{GS} = 0		-1.5	V